

ME12VZ1UABH

1. Features

- 1800Watts peak pulse power (tp = 8/20μs)
- Uni-directional configurations
- Solid-state silicon-avalanche technology
- Capacitance: 110pF typical
- Low clamping voltage
- Low leakage current
- Complies with following standards:
  - — IEC 61000-4-2 (ESD) immunity test
    Air discharge: ±30KV
    Contact discharge: ±30KV
  - — IEC61000-4-4 (EFT) 40A (5/50ns)
  - — IEC61000-4-5(Lightning) 50A (8/20us)

2. Application

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals

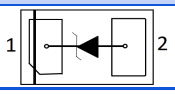
3. Mechanical Data

- Package: DFN1006-2L
- UL Flammability Classification Rating 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

4. Absolute Maximum Rating

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Contact) ESD per IEC 61000-4-2 (Air)	V_{ESD}	±30 ±30	KV
Peak Pulse Power(8/20μs)	P_{PP}	1500	W
Reverse Working Voltage	V_{RWM}	12	V
Maximum Reverse Peak Pulse Current	I_{PP}	50	A
Operating Temperature	T_{OPT}	-55~+125	°C
Storage Temperature	T_{stg}	-55~+150	°C

5. Pinning information

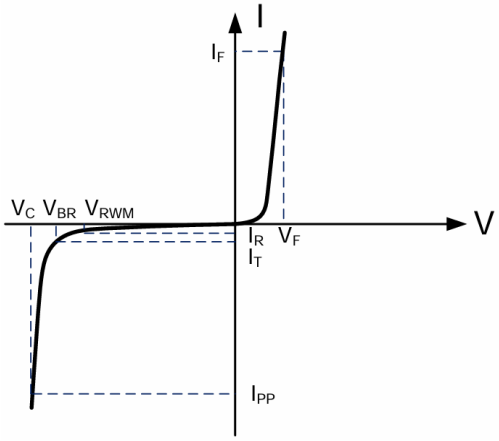
Pin	Symbol	Simplified outline	Equivalent Circuit	Marking	Package
2	Uni			AH	DFN1006-2L

6.Electrical Characteristics(Tamb=25°C)

Parameter	Symbols	Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				12	V
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	13			V
Reverse Leakage Current	I_R	V_{RWM}=12V			1	uA
Clamping Voltage	Vc	I_{pp}=50A , t_p=8/20us			30	V
Junction Capacitance	C_J	V_R =0V ,f=1MHz		110		pF

7.Electrical Parameters

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage@I_{PP}
V_{RWM}	Reverse Working Voltage
I_R	Maximum Reverse Leakage Current
I_T	Test Current
V_{BR}	Breakdown Voltage@I_T
V_F	Forward Voltage
I_F	Forward Test Current



8.Typical Characteristics

Fig.1 8/20us Waveform Per iec6100-4-5

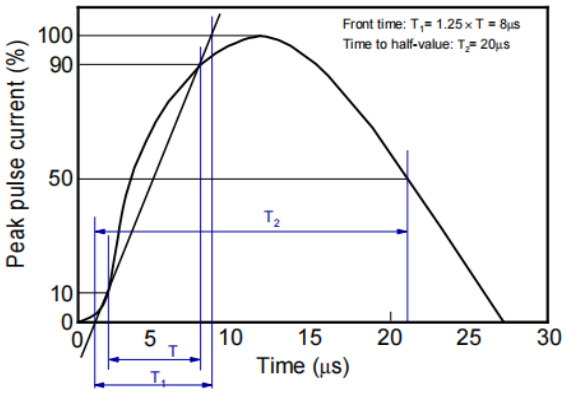


Fig.2 Contact Discharge Current Waveform per IEC61000-4-2

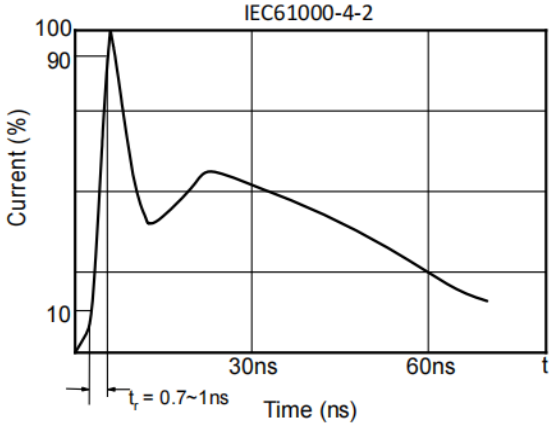


Fig.3 Clamping Voltage Vs. Peak Pulse Current

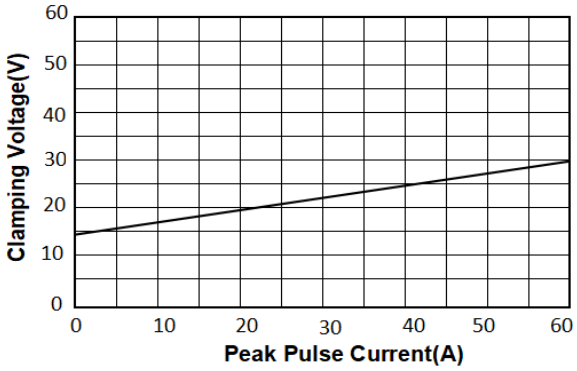
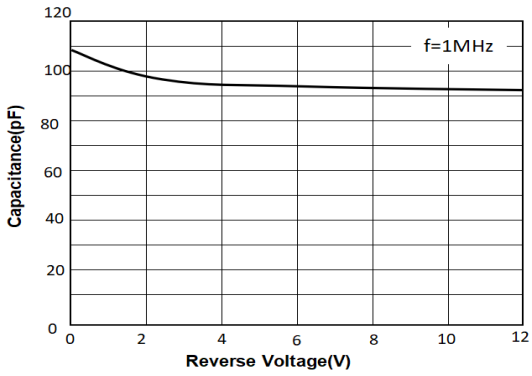
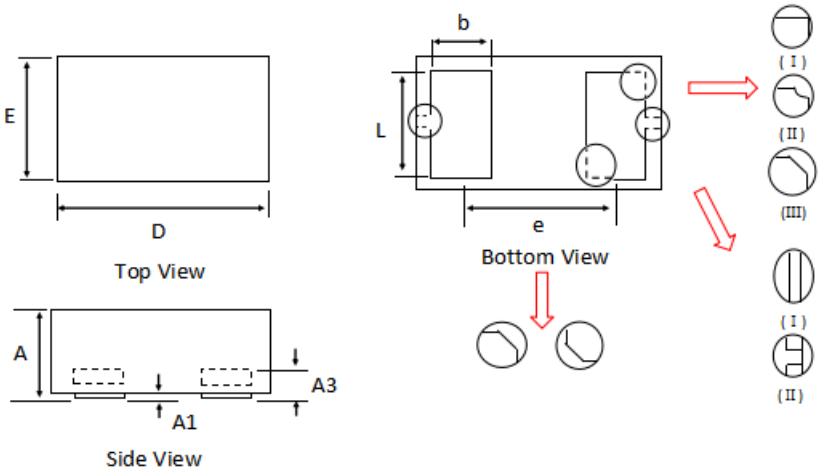


Fig.4 Capacitance VS Reverse Voltage



9.Outline Drawing

DFN1006-2L Package Outline Dimensions



REF	mm	inch
A	0.35~0.55	0.014~0.022
A1	0.00~0.05	0.000~0.002
A3	0.125REF	0.005REF
D	0.95~1.10	0.037~0.043
E	0.55~0.70	0.022~0.028
L	0.45~0.55	0.018~0.022
e	0.65BSC	0.026BSC
b	0.15~0.35	0.006~0.014

10. Reel packing

Package	Reel Size	Reel DIA. (mm)	Q'TY/Reel (pcs)	QTY/Box (pcs)	Q'TY/Carton (pcs)
DFN1006-2L	7'	178	10,000	100,000	400,000

11.Important Notice and Disclaimer

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